



HOKKAIDO UNIVERSITY

# Millimeter-wave Metamaterial Antenna in Standard CMOS Technology

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## Background and Objective

### Background

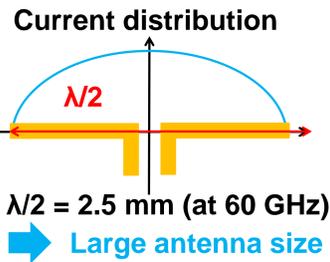
- Wireless communication system
- ✓ Bands of 2.4 and 5 GHz crowded

### Solutions

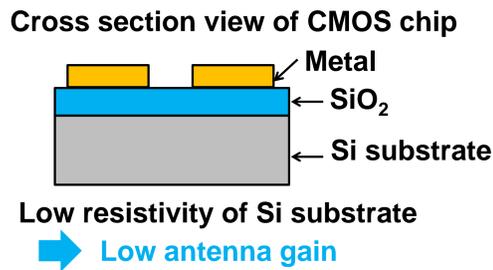
- ✓ Millimeter-wave regions (e.g., 60 GHz)
- ✓ High gain Si on-chip antenna to reduce cost

### Problems

#### Principle of dipole antenna



#### On-chip antenna



### Objective

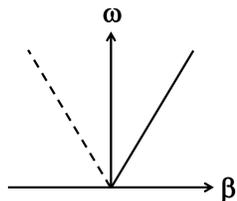
Design and fabricate MM-wave high-gain, small-size on-chip antenna

## Principle

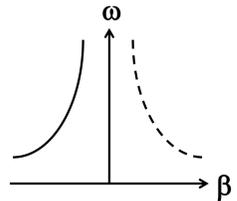
### Metamaterial

Artificial materials that show electromagnetic properties not existing in nature

#### Right-handed region



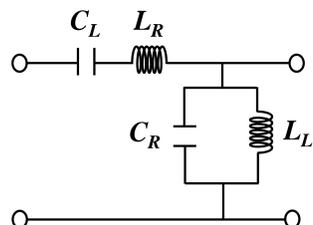
#### Left-handed region



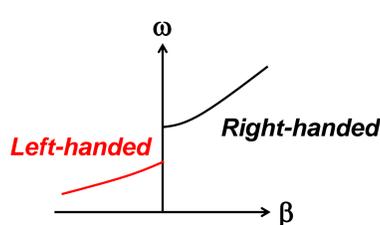
- Radiation frequency inversely proportional to phase constant
- ⇒ Miniaturized antenna size
- ⇒ Increased gain due to reduction in silicon substrate loss
- ✓ Pure left-handed transmission line impossible to fabricate

### Composite right/left-handed (CRLH) theory

#### CRLH transmission line



#### Dispersion diagram of CRLH

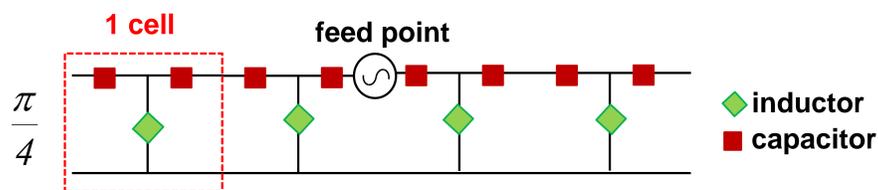


#### Dispersion relation

$$\beta p = \cos^{-1} \left[ 1 - \frac{1}{2} \left( \omega L_R - \frac{1}{\omega C_L} \right) \left( \omega C_R - \frac{1}{\omega L_L} \right) \right]$$

$\beta$ : phase constant      $p$ : length of unit cell

#### Structure of metamaterial antenna



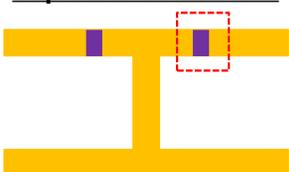
Phase difference between two open ends equals  $\pi$  at 60 GHz

## Fabrication Method

### Antenna Design

Process : TSMC 0.18- $\mu\text{m}$  1P6M mixed signal/RF CMOS

#### Top view of unit cell



#### Cross-sectional view of series capacitor

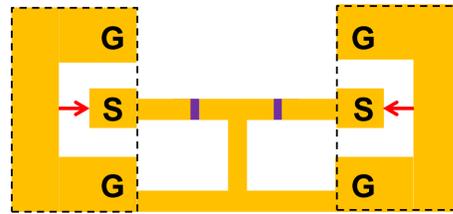


- ✓ Thick top metal used as antenna element (to reduce wire loss)
- ✓ C<sub>L</sub> : MIM capacitor between Metal 5 and Metal 6
- ✓ L<sub>L</sub> : straight line of Metal 6

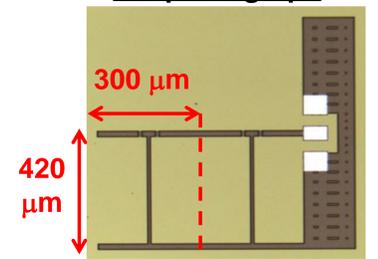
### EM Simulation

Simulator : EMpro (Keysight Tech.)  
using Finite-difference-time-domain (FDTD) method

#### Analysis model for unit cell



#### Die photograph

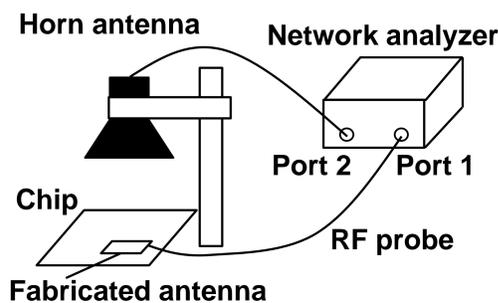


- ✓ Feed points assumed to be GSG pads
- ✓ Calculated rigorous dispersion diagram
- ⇒ Adjust component sizes

## Measurement

### Measurement System

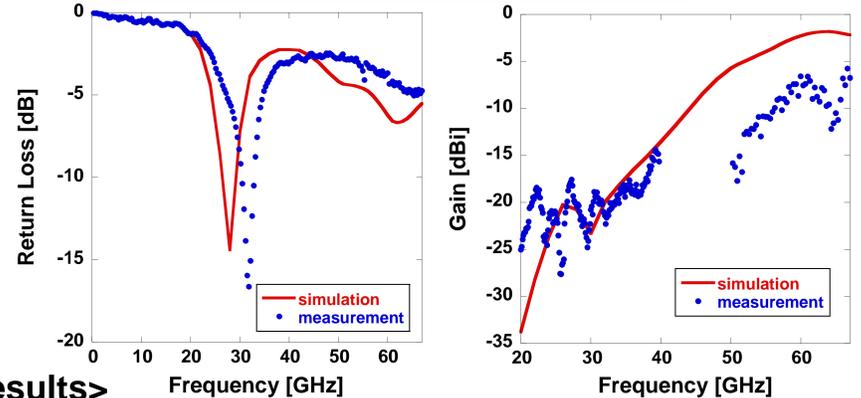
#### Experimental setup



- ✓ Two types of horn antennas (20 - 40 GHz and 50 - 67 GHz)
- ✓ Return loss measured with 1-port calibration method
- ✓ Gain evaluated by taking into account S<sub>21</sub> between two horn antennas and gain of horn antenna

### Results and Discussion

#### Measurement results of fabricated antenna



#### <Results>

|                 | LH mode               |                         | RH mode               |                        |
|-----------------|-----------------------|-------------------------|-----------------------|------------------------|
|                 | simulation            | measurement             | simulation            | measurement            |
| S <sub>11</sub> | -14.4 dB<br>(28 GHz)  | -16.6 dB<br>(31.8 GHz)  | -6.7 dB<br>(62 GHz)   | -5.0 dB<br>(65.3 GHz)  |
| Gain            | -20.8 dBi<br>(28 GHz) | -14.4 dBi<br>(39.3 GHz) | -1.83 dBi<br>(65 GHz) | -5.8 dBi<br>(66.7 GHz) |

#### <Discussion>

- ✓ Measured S<sub>11</sub> shifted about 3 to 6 GHz to higher frequency compared with simulated one
- ✓ Measured gain ~7 dB smaller than simulation in 50 - 67-GHz range
- ⇒ Different radiation patterns between horn antenna and fabricated antenna and/or difference between fabricated silicon substrate resistivity and value (10  $\Omega\text{-cm}$ ) assumed in simulations

## Conclusion

#### Performance comparison

|           | Process     | Gain      | Size   | Configuration |
|-----------|-------------|-----------|--|---------------|
| This work | 180-nm CMOS | -5.8 dBi  | 600 $\mu\text{m}$ $\times$ 420 $\mu\text{m}$   | CRLH monopole |
| [1]       | 65-nm CMOS  | -10 dBi   | 1000 $\mu\text{m}$ $\times$ 300 $\mu\text{m}$  | Dipole        |
| [2]       | 180-nm CMOS | -10.6 dBi | 1100 $\mu\text{m}$ $\times$ 950 $\mu\text{m}$  | Yagi          |
| [3]       | 90-nm CMOS  | -6.0 dBi  | 1300 $\mu\text{m}$ $\times$ 1100 $\mu\text{m}$ | Slot on AMC   |

- [1] T. Hirano, T. Yamaguchi, N. Li, K. Okada, J. Hirokawa, and M. Ando, "60 GHz on-chip dipole antenna with differential feed," *Proc. 2012 APMC*, Dec. 4-7, 2012, pp. 304-306.
- [2] S.-S. Hsu, K.-C. Wei, C.-Y. Hsu, and H. R.-Chuang, "A 60-GHz millimeter-wave CPW-fed Yagi antenna fabricated by using 0.18- $\mu\text{m}$  CMOS technology," *IEEE Electron Device Lett.*, vol. 29, no. 6, pp. 625-627, 2008.
- [3] K. Kang, F. Lin, D.-D. Pham, J. Brinkhoff, C.-H. Heng, Y. X. Guo, and X. Yuan, "A 60-GHz OOK receiver with an on-chip antenna in 90 nm CMOS," *IEEE J. Solid-State Circuits*, vol. 45, no. 9, pp. 1720-1730, 2010.

Successful design and fabrication of MM-wave high gain, small-size on-chip antenna

## Acknowledgement

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